## **Turkish Journal of Physics**

The Absorption Properties of p-Type TIIn, Ga<sub>(1-x)</sub> Se<sub>2</sub> and TIGaSe<sub>2</sub>

**Turkish Journal** 

of

**Physics** 

Bekir GÜRBULAK, Muhammet YILDIRIM, Aytunç ATEŞ, Sehabattin TÜZEMEN, Yahya Kemal YO URTÇU Atatürk Üniversitesi, Fen-Edebiyat Fakültesi, Fizik Bölümü, 25240, Erzurum-TURKEY

Keywords Authors



phys@tubitak.gov.tr

Scientific Journals Home
Page

Abstract: p-TIGaSe $_2$ , p-TIIn $_{0.3}$ Ga $_{0.7}$ Se $_2$  and p-TIIn $_{0.5}$ Ga $_{0.5}$ Se $_2$  single crystals were grown by the modified Bridgman-Stockbarger method in our crystal growth laboratory. The absorption measurements were carried out on p-TIIn $_x$ Ga $_{(1-x)}$ Se $_2$  samples in temperature range 10-300 K in steps of 10 K. The binding energies of p-TIGaSe $_2$ , p-TIIn $_{0.3}$ Ga $_{0.7}$ Se $_2$  and p-TIIn $_{0.5}$  Ga $_{0.5}$  Se $_2$  were obtained as \\ 35.0 meV, 16.5 meV and 14.5 meV, respectively. THe direct band gaps were calculated as 2.244 eV, 2.195 eV, 2.164 eV in p-TIGaSe $_2$ , 2.158 eV, 2.131 eV, 2.098 eV in p-TIIn $_{0.3}$ Ga $_{0.7}$ Se $_2$ , and 2.107 eV, 2.075 eV, 2.019 eV in p-TIIn $_{0.5}$ Ga $_{0.5}$ Se $_2$  respectively, at sample temperatures of 10 K, 140 K and 300 K. The indirect band gaps were calculated as 2.196 eV, 2.127 eV, 2.073 eV in p-TIGaSe $_2$  2.130 eV, 2.101 eV, 2.064 eV in p-TIIn $_{0.3}$ Ga $_{0.7}$ Se $_2$  and 2.090 eV, 2.054 eV, 2.004 eV in p-TIIn $_{0.5}$ Ga $_{0.5}$ Se $_2$  respectively, at 10 K, 140 K and 300 K. There is an abrupt change in the energy peak for p-TIGaSe $_2$  in the temperature range 135-150 K. The values that we obtained from the energy peak change may be at a phase transition temperature.

<u>Key Words:</u>  $TIGaSe_2$ ,  $TIIn_{0.3}Ga_{0.7}Se_2$ ,  $TIIn_{0.5}Ga_{0.5}Se_2$  single crystals, absorption, binding energy, phase transition.

Turk. J. Phys., 24, (2000), 49-62.

Full text: pdf

Other articles published in the same issue: Turk. J. Phys., vol. 24, iss. 1.